General Purpose Transistor

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-40	Vdc
Collector - Base Voltage	V _{CBO}	-40	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	Ic	-200	mAdc
Collector Current - Peak (Note 3)	I _{CM}	-800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @ T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

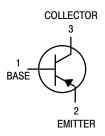
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



2A = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

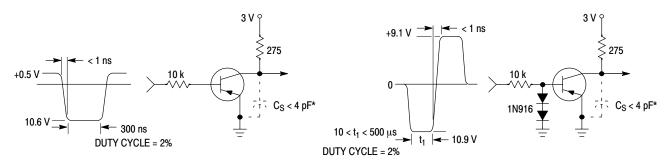
Device	Package	Shipping [†]
MMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charac	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-40	_	Vdc		
Collector – Base Breakdown Voltage ($I_C = -10 \mu Adc, I_E = 0$)	V _{(BR)CBO}	-40	_	Vdc		
Emitter – Base Breakdown Voltage ($I_C = -10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	-5.0	_	Vdc	
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)		I _{BL}	-	-50	nAdc	
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)	I _{CEX}	-	-50	nAdc		
ON CHARACTERISTICS (Note 4)		•	•	•	•	
DC Current Gain		H _{FE}	60 80 100 60 30	- 300 - -	-	
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	- -	-0.25 -0.4	Vdc		
Base – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)	V _{BE(sat)}	-0.65 -	-0.85 -0.95	Vdc		
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product $(I_C = -10 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f)$	f _T	250	_	MHz		
Output Capacitance $(V_{CB} = -5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ M})$	Hz)	C _{obo}	_	4.5	pF	
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 M	Hz)	C _{ibo}	-	10	pF	
Input Impedance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$,	h _{ie}	2.0	12	kΩ		
Voltage Feedback Ratio ($I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc},$	h _{re}	0.1	10	X 10 ⁻⁴		
Small – Signal Current Gain ($I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc},$	h _{fe}	100	400	-		
Output Admittance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$,	h _{oe}	3.0	60	μmhos		
Noise Figure (I _C = $-100 \mu Adc$, V _{CE} = $-5.0 Vdc$,	NF	-	4.0	dB		
SWITCHING CHARACTERISTICS						
Delay Time	(V _{CC} = -3.0 Vdc, V _{BE} = 0.5 Vdc,	t _d	-	35	no	
Rise Time	I _C = -10 mAdc, I _{B1} = -1.0 mAdc)	t _r	-	35	ns	
Storage Time	$(V_{CC} = -3.0 \text{ Vdc}, I_{C} = -10 \text{ mAdc},$	t _s	-	225	ns	
Fall Time	$I_{B1} = I_{B2} = -1.0 \text{ mAdc}$	t _f	-	75	110	

^{4.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

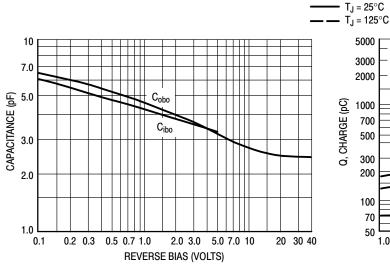


Figure 3. Capacitance

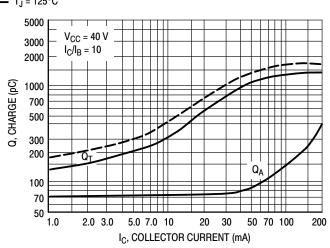


Figure 4. Charge Data

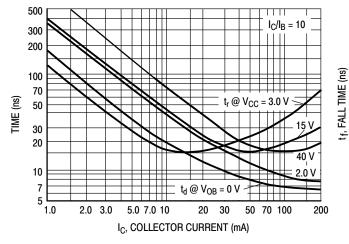


Figure 5. Turn - On Time

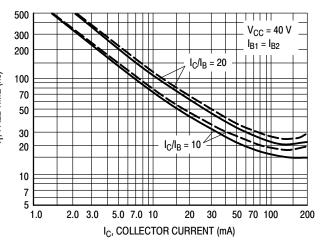
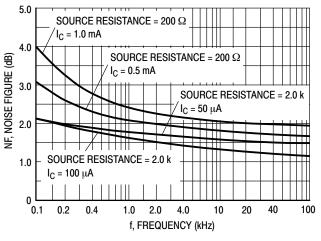


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



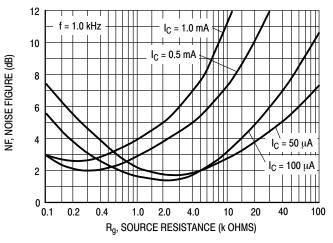
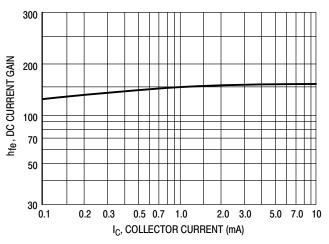


Figure 7.

Figure 8.

h PARAMETERS

 $(V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C})$



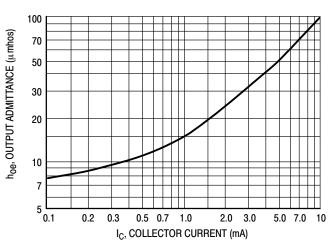
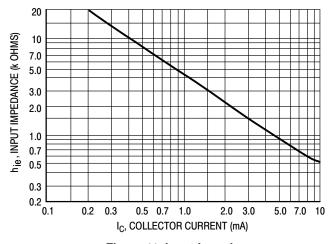


Figure 9. Current Gain

Figure 10. Output Admittance



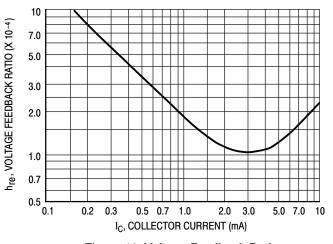


Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

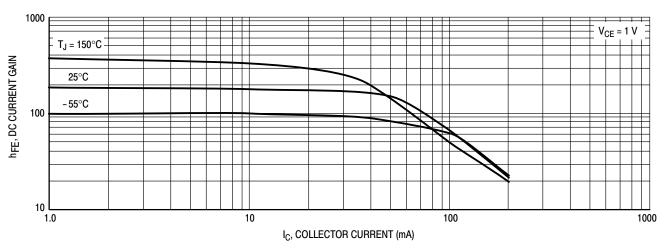


Figure 13. DC Current Gain

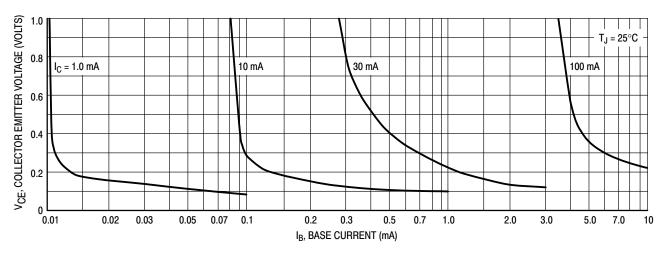


Figure 14. Collector Saturation Region

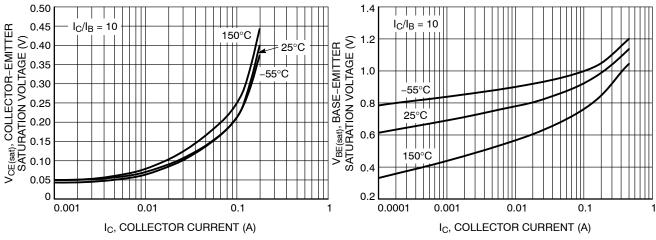


Figure 15. Collector Emitter Saturation Voltage vs. Collector Current

Figure 16. Base Emitter Saturation Voltage vs.
Collector Current

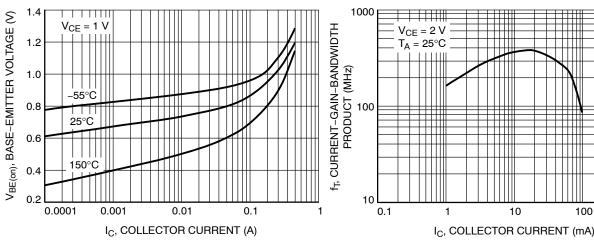


Figure 17. Base Emitter Voltage vs. Collector Current

Figure 18. Current Gain Bandwidth vs. Collector Current

1000

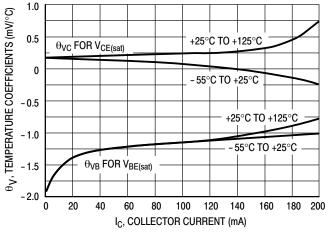


Figure 19. Temperature Coefficients

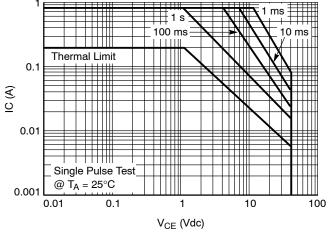
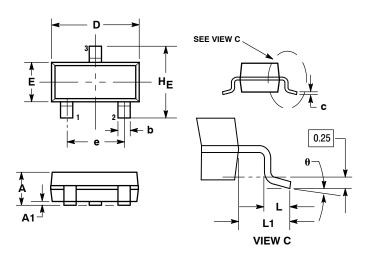


Figure 20. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**

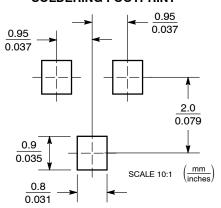


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6: PIN 1. BASE EMITTER COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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